Dual High-Efficiency PWM Step-Down DC/DC Converter

General Description

The RT8020E is a dual high-efficiency Pulse-Width-Modulated (PWM) step-down DC/DC converter. It is capable of delivering 1A output current over a wide input voltage range from 2.5V to 5.5V. The RT8020E is ideally suited for portable electronic devices that are powered by 1-cell Li-ion battery or other power sources within the range such as cellular phones, PDAs and other hand-held devices.

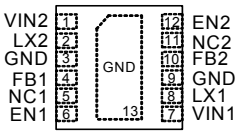
Two operational modes are available : PWM/Low-Dropout auto-switch mode and shutdown mode. Internal synchronous rectifier with low $R_{DS(ON)}$ dramatically reduces conduction loss at PWM mode. No external Schottky diode is required in practical application.

The RT8020E enters Low-Dropout mode when normal PWM cannot provide regulated output voltage by continuously turning on the upper PMOS. The RT8020E enters shutdown mode and consumes less than 0.1μA when the EN pin is pulled low.

The switching ripple is easily smoothed-out by small package filtering elements due to a fixed operation frequency of 1.5MHz. This, along with a small WDFN-12L 3x3 package, provides an ideal solution for small PCB area application. Other features include soft start, lower internal reference voltage with 2% accuracy, over temperature protection, and over current protection.

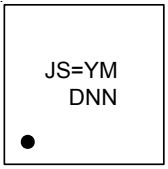
Pin Configurations

(TOP VIEW)



WDFN-12L 3x3

Marking Information



JS= : Product Code

YMDNN : Date code

Features

- **2.5V to 5.5V Input Range**
- **1.2V and 1.8V Fixed Output Voltage**
- **1A Output Current**
- **95% Efficiency**
- **No Schottky Diode Required**
- **50μA Quiescent Current per Channel**
- **1.5MHz Fixed Frequency PWM Operation**
- **Small 12-Lead WDFN Package**
- **RoHS Compliant and Halogen Free**

Applications

- Digital Still Cameras
- Mobile Phones
- Personal Information Appliances
- Wireless and DSL Modems
- MP3 Players
- Portable Instruments

Ordering Information

RT8020E □□

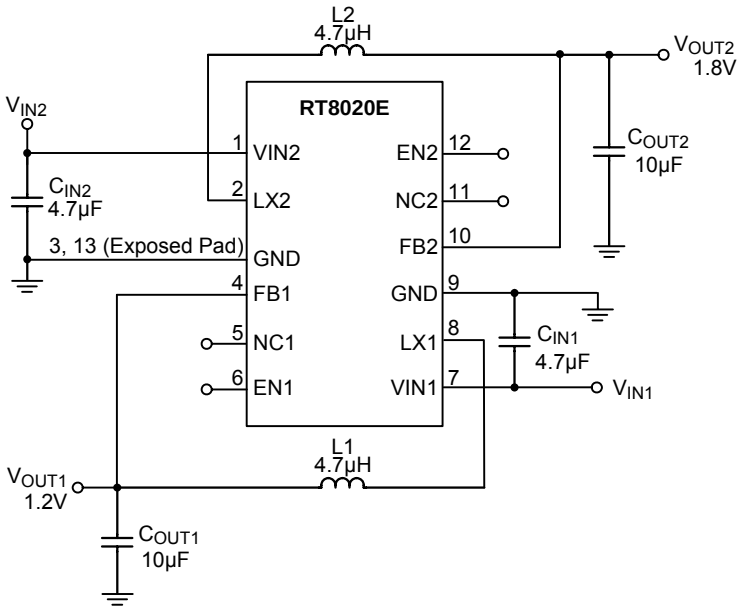
- Package Type
  QW : WDFN-12L 3x3 (W-Type)
- Lead Plating System
  P : Pb Free
  G : Green (Halogen Free and Pb Free)
- Fixed Output Voltage : VOUT1/VOUT2
  1.2V/1.8V

Note :

Richtek products are :

- RoHS compliant and compatible with the current requirements of IPC/JEDEC J-STD-020.
- Suitable for use in SnPb or Pb-free soldering processes.

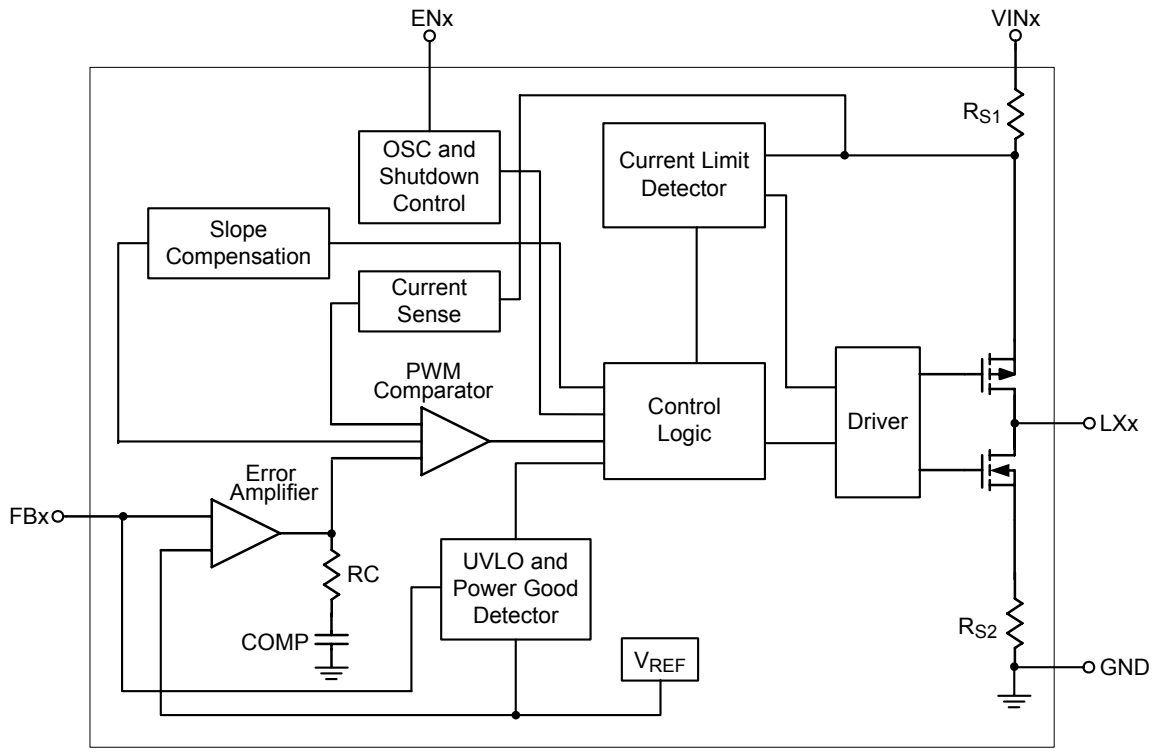
Typical Application Circuit



Functional Pin Description

Pin No.	Pin Name	Pin Function
1	VIN2	Power Input of Channel 2.
2	LX2	Pin for Switching of Channel 2.
3, 9, 13 (Exposed Pad)	GND	Ground. The exposed pad must be soldered to a large PCB and connected to GND for maximum power dissipation.
4	FB1	Feedback of Channel 1.
5, 11	NC1, NC2	No Internal Connection or Connect to V_{IN}.
6	EN1	Chip Enable of Channel 1 (Active High). $V_{EN1} \leqq V_{IN1}$.
7	VIN1	Power Input of Channel 1.
8	LX1	Pin for Switching of Channel 1.
10	FB2	Feedback of Channel 2.
12	EN2	Chip Enable of Channel 2 (Active High). $V_{EN2} \leqq V_{IN2}$.

Function Block Diagram



Absolute Maximum Ratings (Note 1)

- Supply Input Voltage, V_{IN1}, V_{IN2} ---------- –0.3V to 6.5V
- EN1, FB1, LX1, EN2, FB2 and LX2 Pin Voltage ---------- –0.3V to V_{IN} + 0.3V
- Power Dissipation, P_D @ T_A = 25°C
  WDFN-12L 3x3 ---------- 1.667W
- Package Thermal Resistance (Note 2)
  WDFN-12L 3x3, θ_{JA} ---------- 60°C/W
  WDFN-12L 3x3, θ_{JC} ---------- 8.2°C/W
- Lead Temperature (Soldering, 10 sec.) ---------- 260°C
- Junction Temperature ---------- 150°C
- Storage Temperature Range ---------- –65°C to 150°C
- ESD Susceptibility (Note 3)
  HBM (Human Body Mode) ---------- 2kV
  MM (Machine Mode) ---------- 200V

Recommended Operating Conditions (Note 4)

- Supply Input Voltage, V_{IN1}, V_{IN2} ---------- 2.5V to 5.5V
- Junction Temperature Range ---------- –40°C to 125°C
- Ambient Temperature Range ---------- –40°C to 85°C

Electrical Characteristics

(V_{IN} = 3.6V, V_{OUT} = 1.8V, L = 4.7µH, C_{IN} = 4.7µF, C_{OUT} = 10µF, I_{MAX}= 1A, T_A = 25°C, unless otherwise specified)

Parameter		Symbol	Test Conditions		Min	Typ	Max	Unit
Channel 1 and Channel 2								
Under Voltage Lock Out threshold		V_{UVLO}			--	1.8	--	V
Hysteresis					--	0.1	--	V
Quiescent Current		I_Q	I_{OUT} = 0mA, V_{FB} = V_{REF} + 5%		--	50	70	µA
Shutdown Current		I_{SHDN}	EN = GND		--	0.1	1	µA
Output Voltage Accuracy		ΔV_{OUT1}	V_{IN1} = 2.5V to 5.5V, V_{OUT1} = 1.2V 0A < I_{OUT1} < 1A		–2	--	2	%
		ΔV_{OUT2}	V_{IN2} = 2.5 to 5.5V, V_{OUT2} = 1.8V 0A < I_{OUT2} < 1A		–2	--	2	%
FB Input Current		I_{FB}	V_{FB} = V_{IN}		–50	--	50	nA
$R_{DS(ON)}$ of P-MOSFET		$R_{DS(ON)_P}$	I_{OUT} = 200mA	V_{IN} = 2.5V	--	0.38	--	Ω
				V_{IN} = 3.6V	--	0.28	--	
$R_{DS(ON)}$ of N-MOSFET		$R_{DS(ON)_N}$	I_{OUT} = 200mA	V_{IN} = 2.5V	--	0.35	--	Ω
				V_{IN} = 3.6V	--	0.25	--	
P-Channel Current Limit		I_{LIM_P}	V_{IN} = 2.5V to 5.5 V		1.4	1.5	2	A
EN Input Threshold Voltage	Logic-High	V_{IH}	V_{IN} = 2.5V to 5.5V		1.5	--	V_{IN}	V
	Logic-Low	V_{IL}	V_{IN} = 2.5V to 5.5V		--	--	0.4	
Oscillator Frequency		f_{OSC}	V_{IN} = 3.6V, I_{OUT} = 100mA		1.2	1.5	1.8	MHz

To be continued

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Thermal Shutdown Temperature	T_{SD}		--	160	--	°C
Maximum Duty Cycle	D_{MAX}		100	--	--	%
LX Leakage Current	I_{LX}	V_{IN} = 3.6V, V_{LX} = 0V or V_{LX} = 3.6V	−1	--	1	μA

Note 1. Stresses listed as the above "Absolute Maximum Ratings" may cause permanent damage to the device. These are for stress ratings. Functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may remain possibility to affect device reliability.

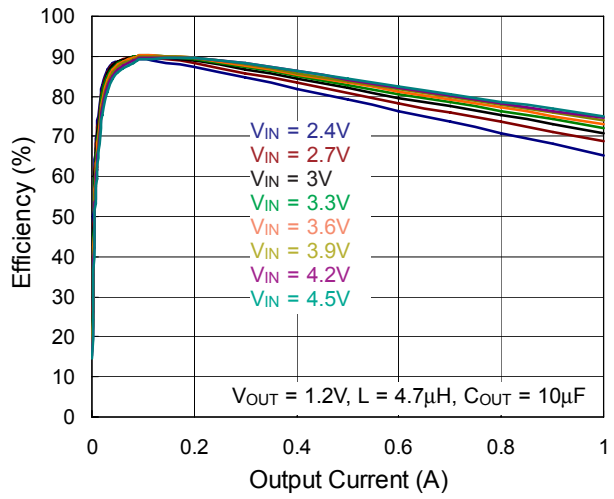
Note 2. θ_{JA} is measured in natural convection at T_A = 25°C on a high effective thermal conductivity four-layer test board of JEDEC 51-7 thermal measurement standard. The measurement case position of θ_{JC} is on the exposed pad of the package.

Note 3. Devices are ESD sensitive. Handling precaution recommended.

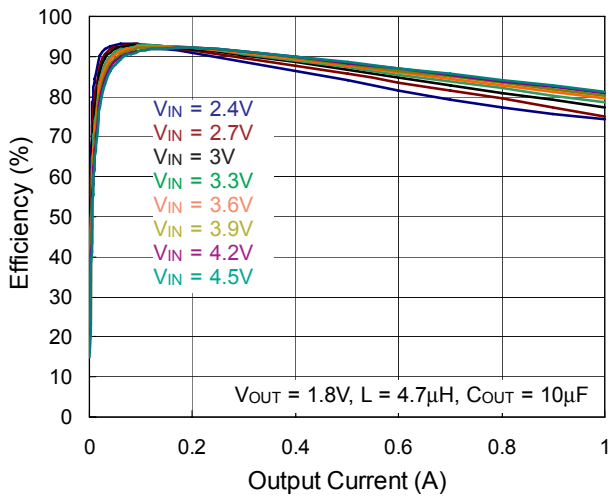
Note 4. The device is not guaranteed to function outside its operating conditions.

Typical Operating Characteristics

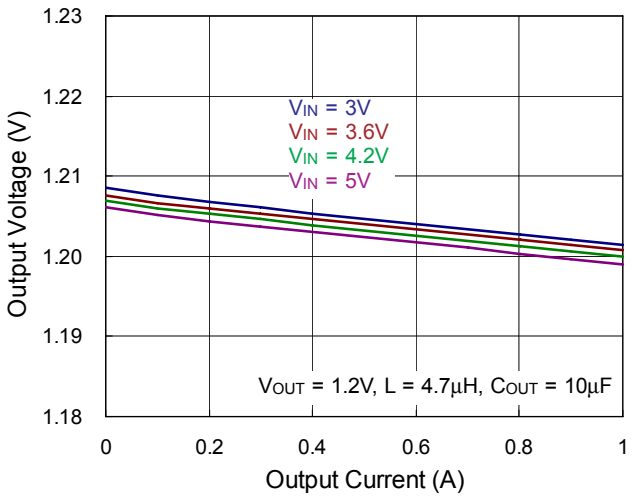
CH1 Efficiency vs. Output Current



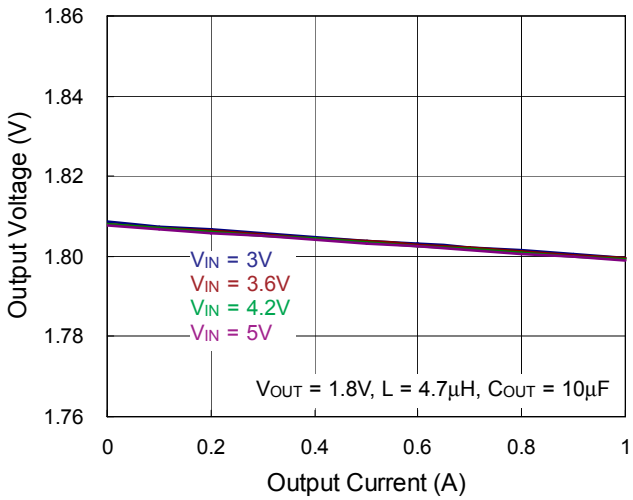
CH2 Efficiency vs. Output Current



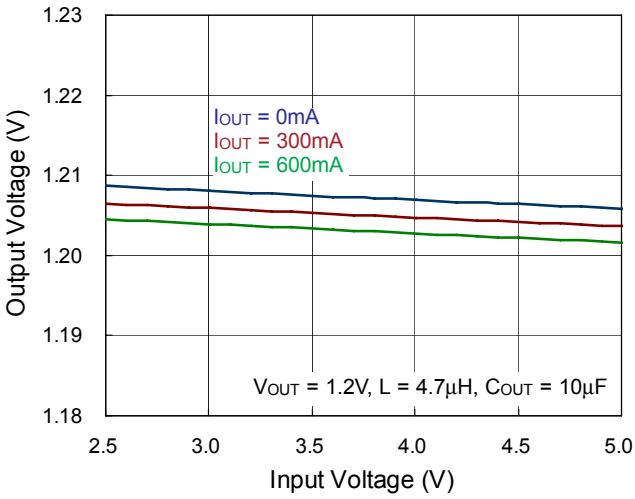
CH1 Output Voltage vs. Output Current



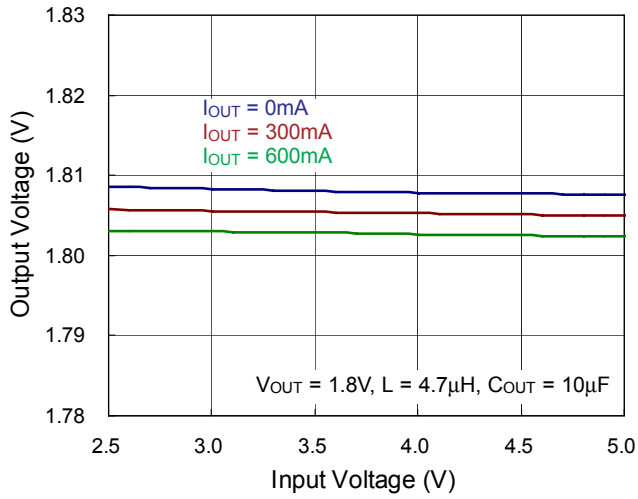
CH2 Output Voltage vs. Output Current



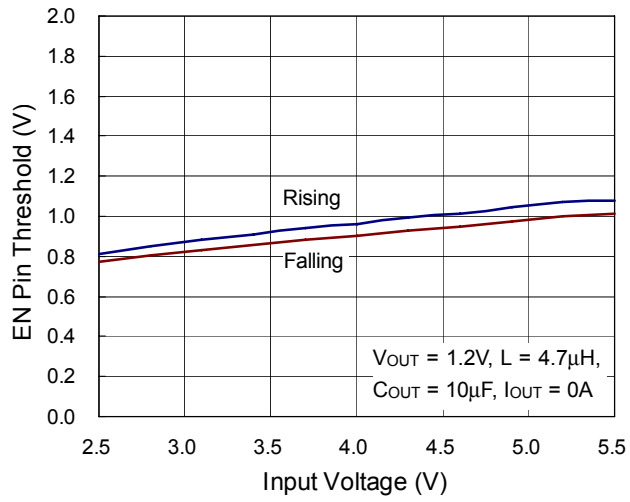
CH1 Output Voltage vs. Input Voltage



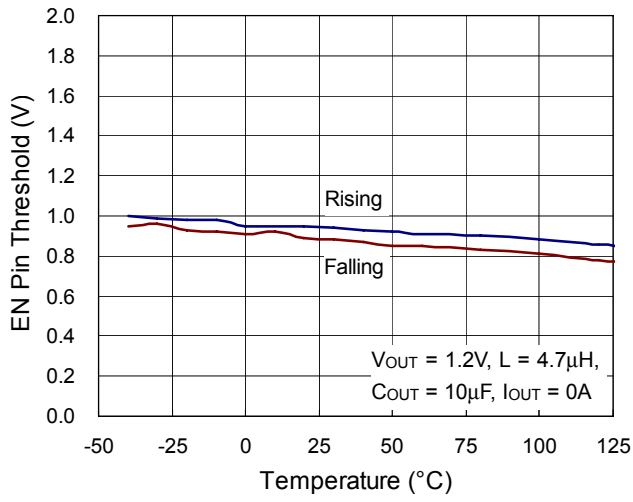
CH2 Output Voltage vs. Input Voltage



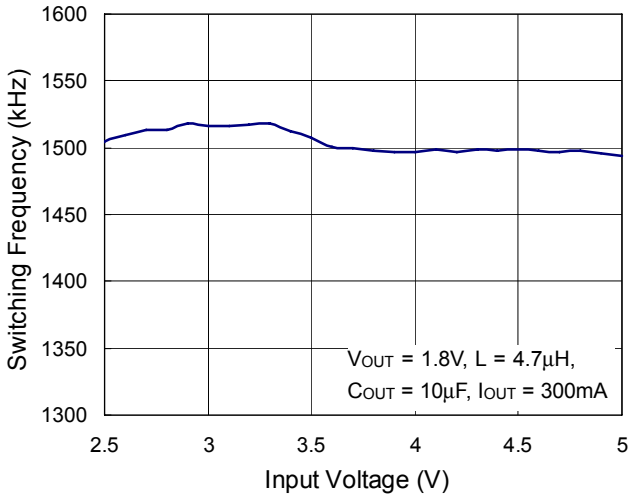
EN Pin Threshold vs. Input Voltage



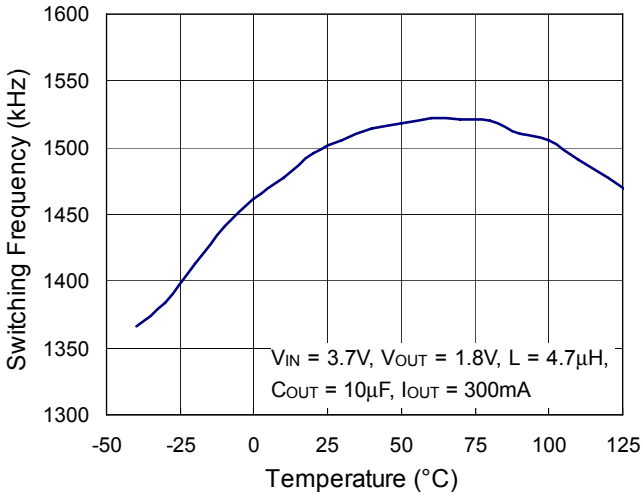
EN Pin Threshold vs. Temperature



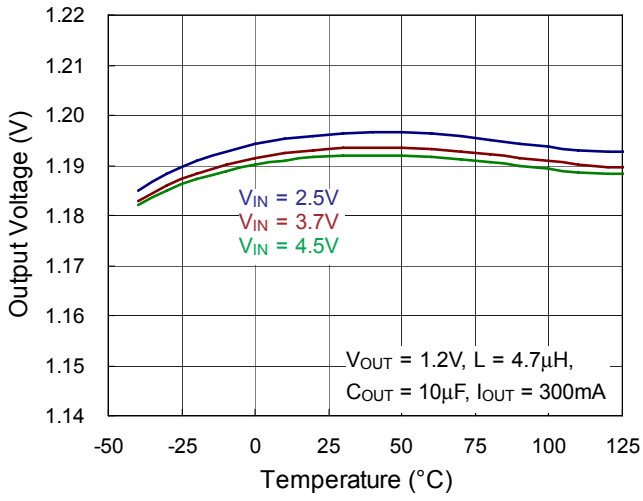
Switching Frequency vs. Input Voltage



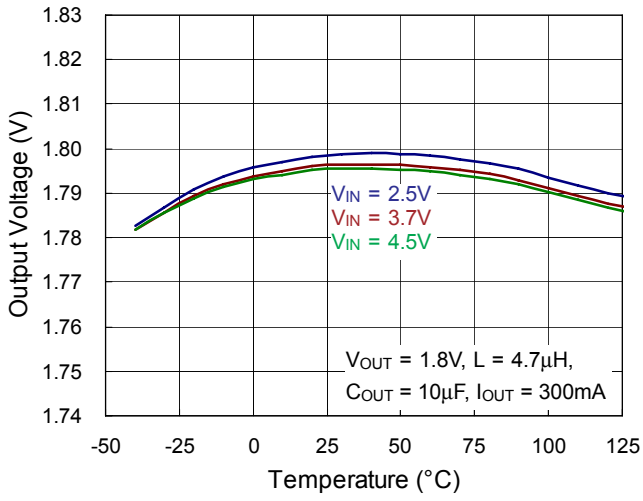
Switching Frequency vs. Temperature



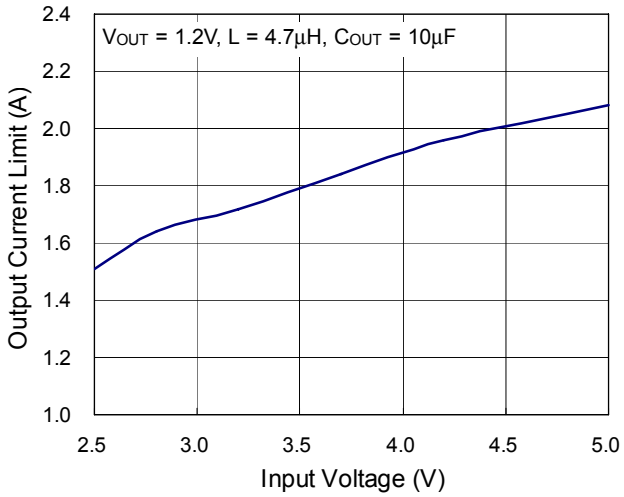
CH1 Output Voltage vs. Temperature



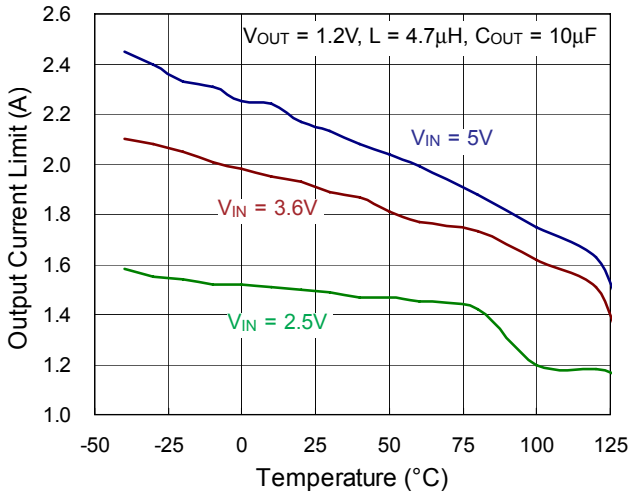
CH2 Output Voltage vs. Temperature



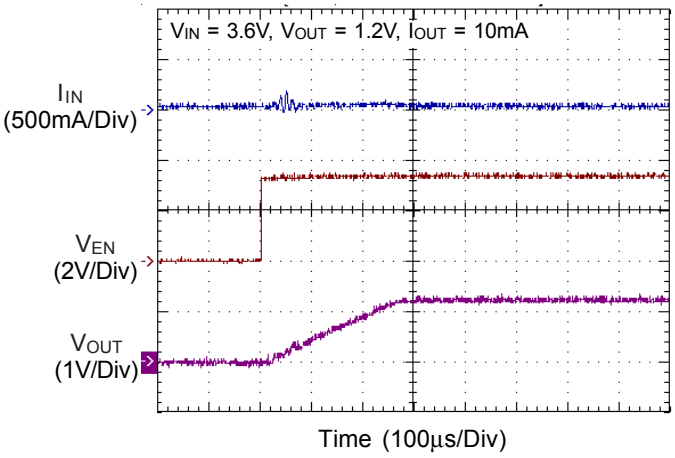
Output Current Limit vs. Input Voltage



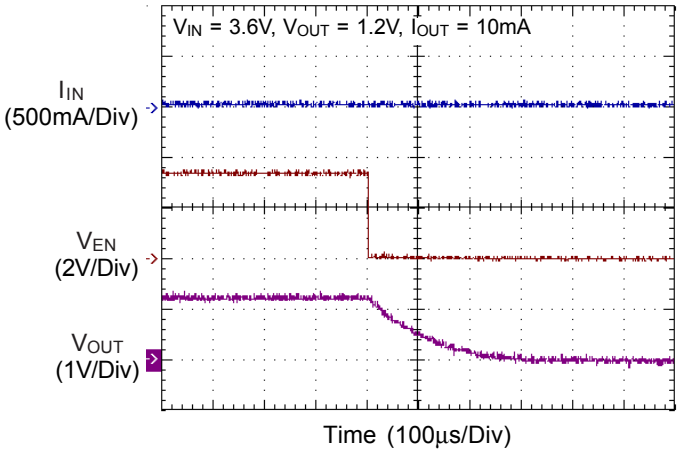
Output Current Limit vs. Temperature



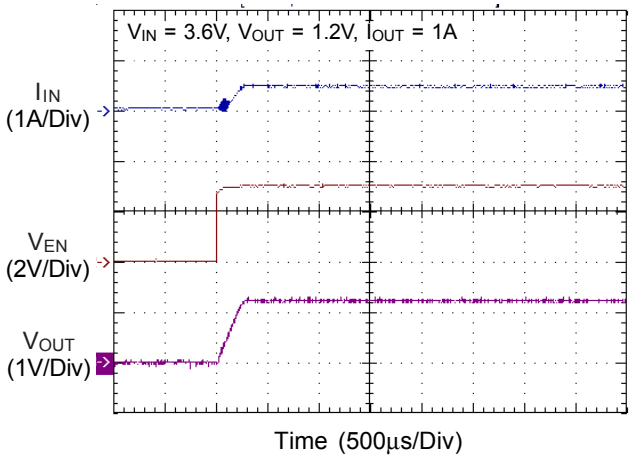
CH1 Power On from EN



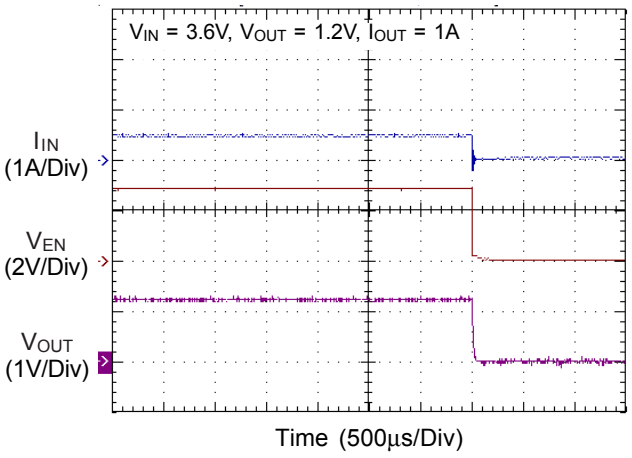
CH1 Power Off from EN



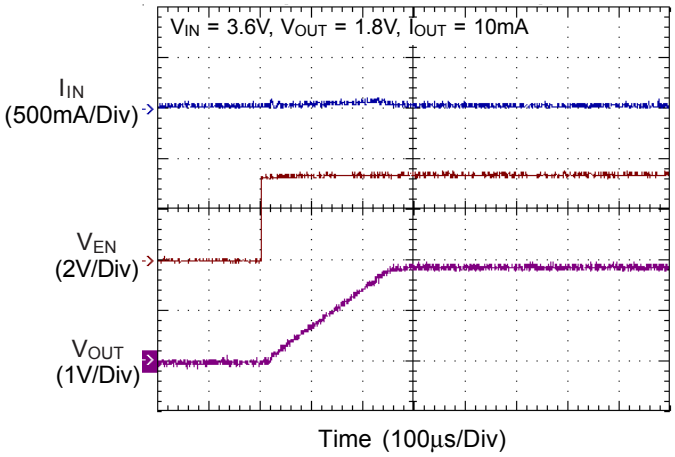
CH1 Power On from EN



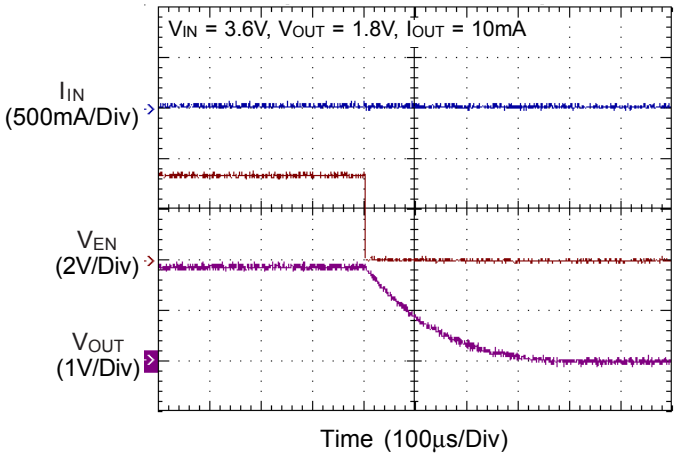
CH1 Power Off from EN



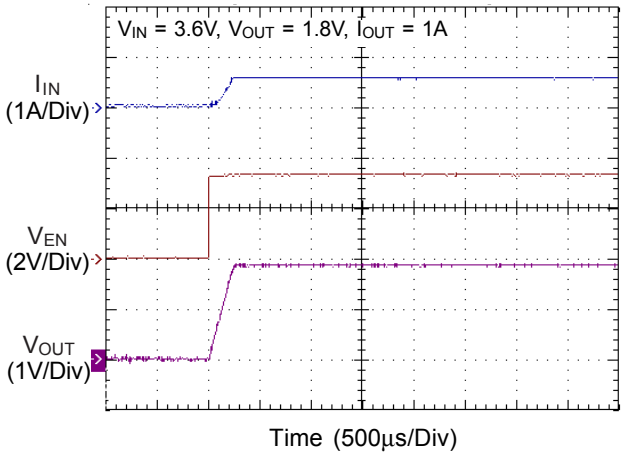
CH2 Power On from EN



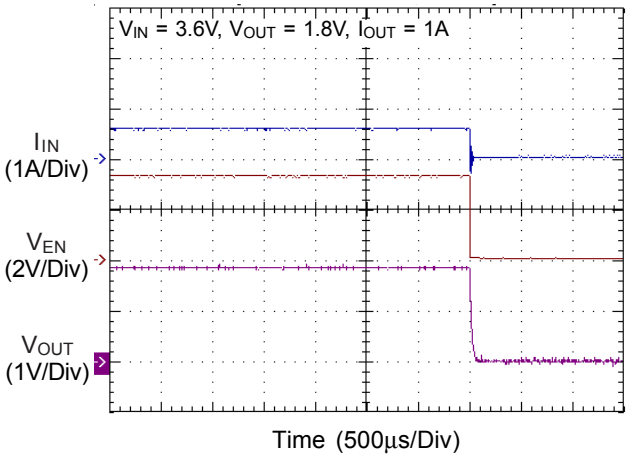
CH2 Power Off from EN



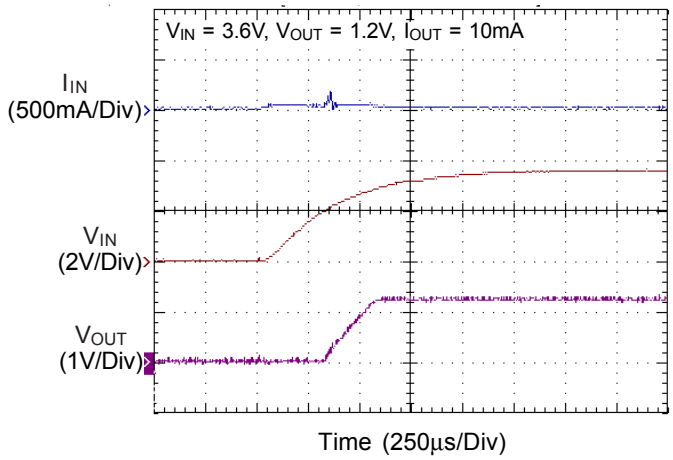
CH2 Power On from EN



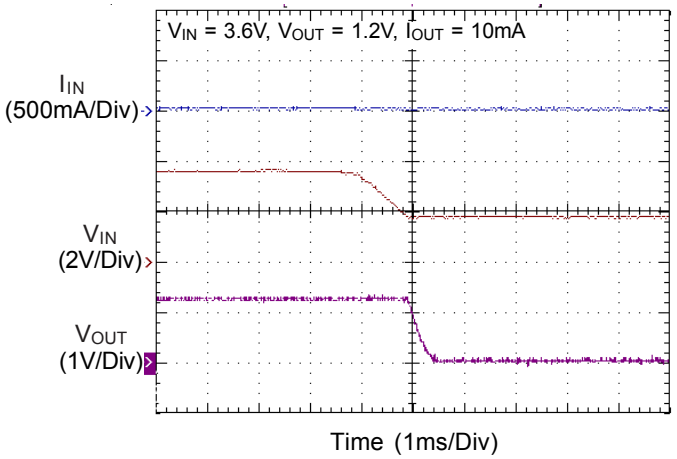
CH2 Power Off from EN



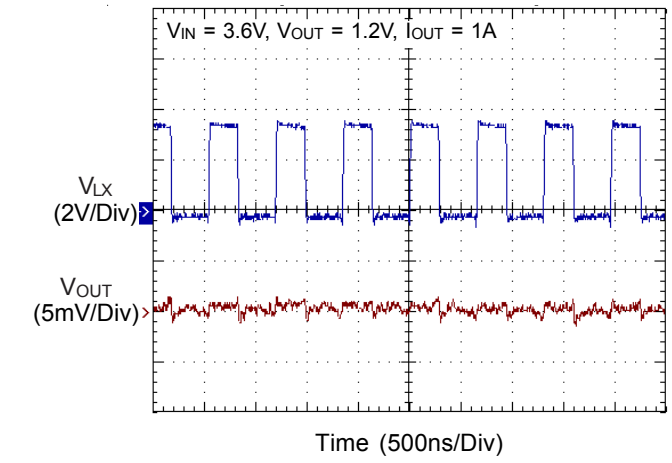
Power On from V_{IN}



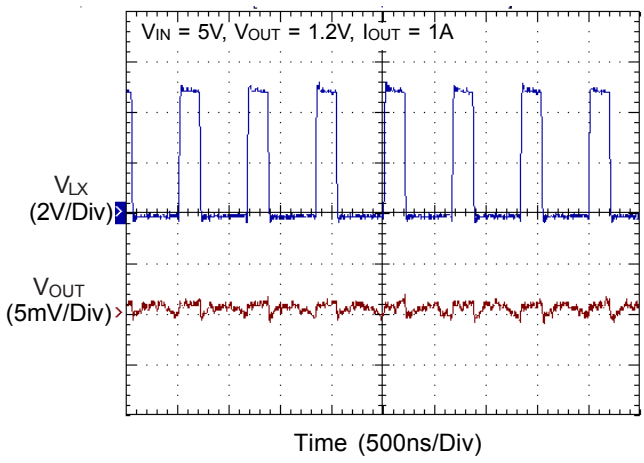
Power Off from V_{IN}



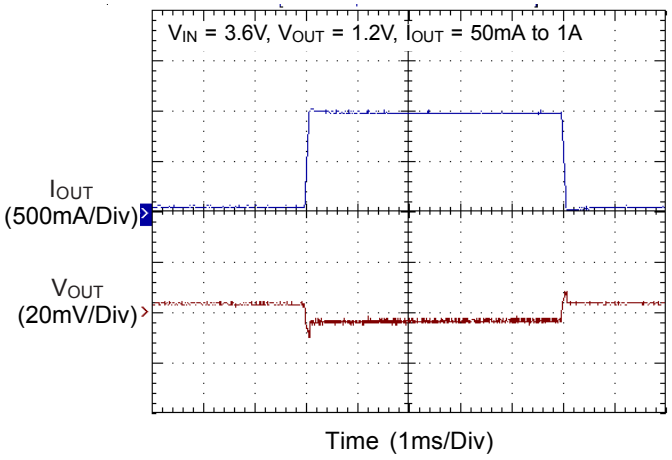
Output Voltage Ripple



Output Voltage Ripple



Load Transient Response



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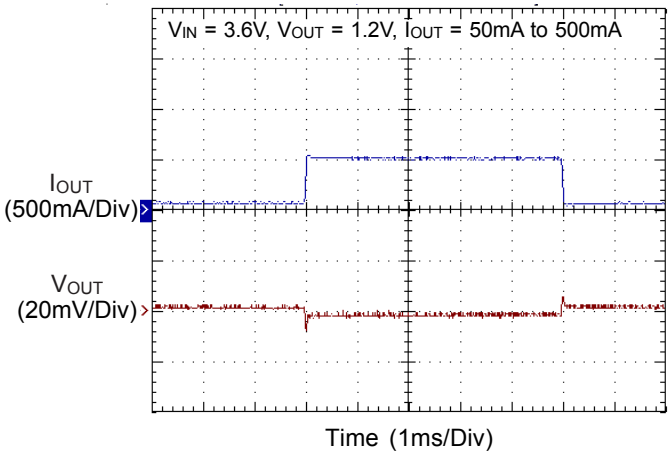
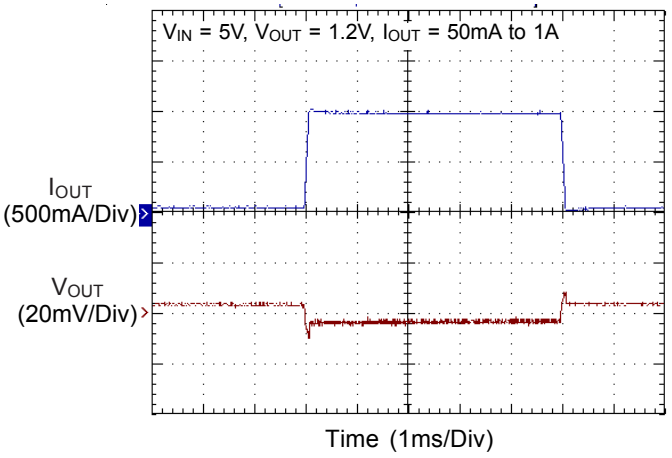
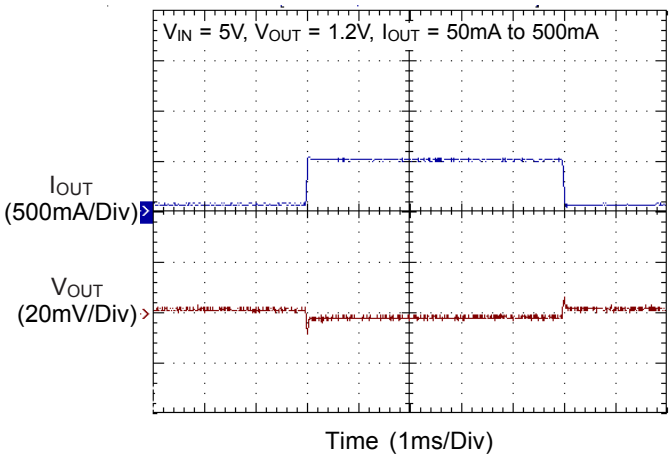


Load Transient Response



Load Transient Response



Applications Information

The basic RT8020E application circuit is shown in Typical Application Circuit. External component selection is determined by the maximum load current and begins with the selection of the inductor value and operating frequency followed by C_{IN} and C_{OUT}.

Inductor Selection

For a given input and output voltage, the inductor value and operating frequency determine the ripple current. The ripple current ΔI_L increases with higher V_{IN} and decreases with higher inductance.

$$\Delta I_L = \left[\frac{V_{OUT}}{f \times L}\right] \times \left[1 - \frac{V_{OUT}}{V_{IN}}\right]$$

Having a lower ripple current reduces the ESR losses in the output capacitors and the output voltage ripple. Highest efficiency operation is achieved at low frequency with small ripple current. This, however, requires a large inductor.

A reasonable starting point for selecting the ripple current is $\Delta I_L = 0.4(I_{MAX})$. The largest ripple current occurs at the highest V_{IN}. To guarantee that the ripple current stays below a specified maximum, the inductor value should be chosen according to the following equation :

$$L = \left[\frac{V_{OUT}}{f \times \Delta I_{L(MAX)}}\right] \times \left[1 - \frac{V_{OUT}}{V_{IN(MAX)}}\right]$$

Inductor Core Selection

Once the value for L is known, the type of inductor can be selected. High efficiency converters generally cannot afford the core loss found in low cost powdered iron cores, thus, limiting the use to more expensive ferrite or permalloy cores. Actual core loss is independent of core size for a fixed inductor value, but it is very dependent on the inductance selected. As the inductance increases, core losses decrease. However, increased inductance requires more turns of wire and therefore higher copper losses.

Ferrite designs have very low core losses and are preferred at high switching frequencies, thus allowing design goals to concentrate on copper loss and saturation prevention. Ferrite core material saturates "hard", which means that inductance collapses abruptly when the peak design current is exceeded.

This results in an abrupt increase in inductor ripple current and consequent output voltage ripple.

Do not allow the core to saturate!

Different core materials and shapes will change the size/current and price/current relationship of an inductor. Toroid or shielded pot cores in ferrite or permalloy materials are small and don't radiate energy but generally cost more than powdered iron core inductors with similar characteristics. The choice of which type of inductor to use mainly depends on the price vs. size requirements and any radiated field/EMI requirements.

C_{IN} and C_{OUT} Selection

The input capacitance, C_{IN}, is needed to filter the trapezoidal current at the source of the top MOSFET. To prevent large ripple voltage, a low ESR input capacitor sized for the maximum RMS current should be used. RMS current is given by :

$$I_{RMS} = I_{OUT(MAX)} \frac{V_{OUT}}{V_{IN}} \sqrt{\frac{V_{IN}}{V_{OUT}} - 1}$$

This formula has a maximum at $V_{IN} = 2V_{OUT}$, where $I_{RMS} = I_{OUT}/2$. This simple worst-case condition is commonly used for design because even significant deviations do not result in much difference. Note that ripple current ratings from capacitor manufacturers are often based on a life time of only 2000 hours, which makes it advisable to further de-rate the capacitor or choose a capacitor rated at a higher temperature than required. Several capacitors may also be paralleled to meet the size or height requirements in the design.

The selection of C_{OUT} is determined by the effective series resistance (ESR) that is required to minimize voltage ripple and load step transients, as well as by the amount of bulk capacitance that is necessary to ensure that the control loop is stable. Loop stability can be checked by viewing the load transient response as described in a later section. The output ripple, ΔV_{OUT}, is determined by :

$$\Delta V_{OUT} \leq \Delta I_L \left[ESR + \frac{1}{8fC_{OUT}}\right]$$

The output ripple is highest at maximum input voltage since ΔI_L increases with input voltage. Multiple capacitors placed in parallel may be needed to meet the ESR and RMS current handling requirements. Dry tantalum, special polymer, aluminum electrolytic and ceramic capacitors are all available in surface mount packages. Special polymer capacitors offer very low ESR, but have lower capacitance density than other types. Tantalum capacitors have the highest capacitance density, but it is important to only use types that have been surge tested for use in switching power supplies. Aluminum electrolytic capacitors have significantly higher ESR, but can be used in cost-sensitive applications provided that consideration is given to ripple current ratings and long-term reliability. Ceramic capacitors have excellent low ESR characteristics, but can have a high voltage coefficient and audible piezoelectric effects. The high Q of ceramic capacitors with trace inductance can also lead to significant ringing.

Using Ceramic Input and Output Capacitors

Higher value, lower cost ceramic capacitors are now becoming available in smaller case sizes. Their high ripple current, high voltage rating and low ESR make them ideal for switching regulator applications. However, care must be taken when these capacitors are used at the input and output. When a ceramic capacitor is used at the input and the power is supplied by a wall adapter through long wires, a load step at the output can induce ringing at the input, V_{IN}. At best, this ringing can couple to the output and be mistaken as loop instability. At worst, a sudden inrush of current through the long wires can potentially cause a voltage spike at V_{IN} large enough to damage the part.

Efficiency Considerations

The efficiency of a switching regulator is equal to the output power divided by the input power times 100%. It is often useful to analyze individual losses to determine what is limiting the efficiency and which change would produce the most improvement. Efficiency can be expressed as :

Efficiency = 100% – (L1+ L2+ L3+...)

where L1, L2, etc. are the individual losses as a percentage of input power. Although all dissipative elements in the circuit produce losses, two main sources usually account for most of the losses : V_{IN} quiescent current and I^2R losses.

The V_{IN} quiescent current loss dominates the efficiency loss at very low load currents whereas the I^2R loss dominates the efficiency loss at medium to high load currents. In a typical efficiency plot, the efficiency curve at very low load currents can be misleading since the actual power lost is of no consequence.

1.The V_{IN} quiescent current appears due to two components : the DC bias current and the gate charge currents. The gate charge current results from switching the gate capacitance of the internal power MOSFET switches. Each time the gate is switched from high to low to high again, a packet of charge ΔQ moves from V_{IN} to ground.

The resulting $\Delta Q/\Delta t$ is the current out of V_{IN} that is typically larger than the DC bias current. In continuous mode,

$I_{GATECHG} = f(Q_T + Q_B)$

where Q_T and Q_B are the gate charges of the internal top and bottom switches. Both the DC bias and gate charge losses are proportional to V_{IN} and thus their effects will be more pronounced at higher supply voltages.

2. I^2R losses are calculated from the resistances of the internal switches, R_{SW} and external inductor, R_L. In continuous mode the average output current flowing through inductor L is "chopped" between the main switch and the synchronous switch. Thus, the series resistance looking into the LX pin is a function of both top and bottom MOSFET $R_{DS(ON)}$ as well as the duty cycle (DC). The equation is shown below :

$R_{SW} = R_{DS(ON)TOP} \times DC + R_{DS(ON)BOT} \times (1 - DC)$

The $R_{DS(ON)}$ for both the top and bottom MOSFETs can be obtained from the Typical Performance Characteristics curves. Thus, to obtain I^2R losses, simply add R_{SW} to R_L and multiply the result by the square of the average output current. Other losses including C_{IN} and C_{OUT} ESR dissipative losses and inductor core losses generally account for less than 2% of the total loss.

Checking Transient Response

The regulator loop response can be checked by looking at the load transient response. Switching regulators take

several cycles to respond to a step in load current. When a load step occurs, V_{OUT} immediately shifts by an amount equal to ΔI_{LOAD} (ESR), where ESR is the effective series resistance of C_{OUT}. ΔI_{LOAD} also begins to charge or discharge C_{OUT}, generating a feedback error signal used by the regulator to return V_{OUT} to its steady-state value. During this recovery time, V_{OUT} can be monitored for overshoot or ringing which would indicate a stability problem.

Thermal Considerations

The maximum power dissipation depends on the thermal resistance of IC package, PCB layout, rate of surrounding airflow, and difference between junction and ambient temperature. The maximum power dissipation can be calculated by the following formula :

$P_{D(MAX)} = (T_{J(MAX)} - T_A) / \theta_{JA}$

where $T_{J(MAX)}$ is the maximum junction temperature, T_A is the ambient temperature and θ_{JA} is the junction to ambient thermal resistance. For recommended operating conditions specification of the RT8020E DC/DC converter, $T_{J(MAX)}$ is the maximum junction temperature of the die and T_A is the ambient temperature. The junction to ambient thermal resistance θ_{JA} is layout dependent. For WDFN-12L 3x3 packages, the thermal resistance, θ_{JA}, is 60°C/W on a standard JEDEC 51-7 four-layer thermal test board. The maximum power dissipation at T_A = 25°C can be calculated by the following formula :

$P_{D(MAX)}$ = (125°C – 25°C) / (60°C/W) = 1.667W for WDFN-12L 3x3 package

The maximum power dissipation depends on the operating ambient temperature for fixed $T_{J(MAX)}$ and thermal resistance, θ_{JA}. For the RT8020E package, the derating curves in Figure 1 allows the designer to see the effect of rising ambient temperature on the maximum power dissipation.

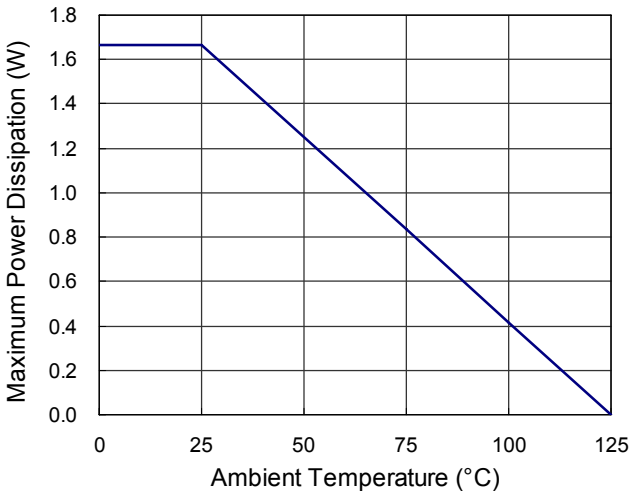


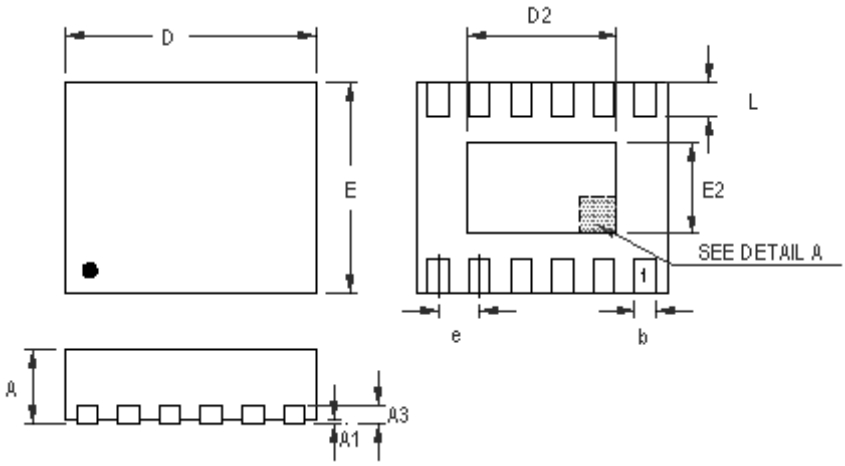
Figure 1. Derating Curve for RT8020E Package

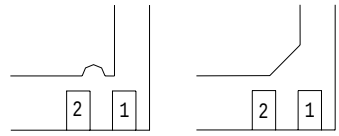
Layout Considerations

Follow the PCB layout guidelines for optimal performance of the RT8020E.

- For the main current paths, keep their traces short and wide.
- Place the input capacitor as close as possible to the device pins (VIN and GND).
- LX node experiences high frequency voltage swing and should be kept in a small area. Keep analog components away from LX node to prevent stray capacitive noise pick-up.
- Connect feedback network behind the output capacitors. Keep the loop area small. Place the feedback components near the RT8020E.
- Connect all analog grounds to a command node and then connect the command node to the power ground behind the output capacitors.

Outline Dimension





DETAIL A

Pin #1 ID and Tie Bar Mark Options

Note : The configuration of the Pin #1 identifier is optional, but must be located within the zone indicated.

Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.700	0.800	0.028	0.031
A1	0.000	0.050	0.000	0.002
A3	0.175	0.250	0.007	0.010
b	0.150	0.250	0.006	0.010
D	2.950	3.050	0.116	0.120
D2	2.300	2.650	0.091	0.104
E	2.950	3.050	0.116	0.120
E2	1.400	1.750	0.055	0.069
e	0.450		0.018	
L	0.350	0.450	0.014	0.018

W-Type 12L DFN 3x3 Package

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